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**PCN # 110**

**Notification Date:**
**21 April 2009**

# Process Change Notice

**Parts Affected:**
Chip process CPD64, Low Leakage Diode discrete semiconductors, wafers, and die in chip form.

**Extent of Change:**
The overall wafer diameter is being increased from 4 inch to 5 inch.
The overall die thickness is being reduced from 8 mils to 5.9 mils

**Reason for Change:**
Process transfer from the 4” wafer fab to the 5” wafer fab.

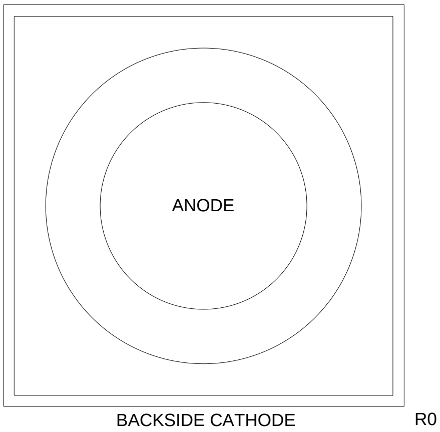
**Effect of Change:**
This change does not affect the electrical characteristics of any device.

**Effective Date of Change:**
Existing inventory will be shipped until depleted.

**Sample Availability:**
Please contact Salesperson or Manufacturer’s Representative.

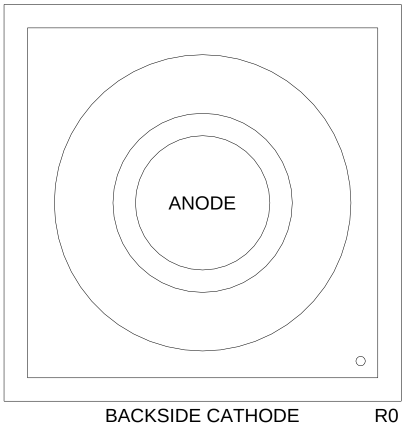
**Figures:**

**Figure 1: CPD64 Chip Geometry**



| | |
|---|---|
| Die Size: | 17.5 x 17.5 mils |
| Die Thickness: | 8.0 mils |
| Bond Pad Area (Anode): | 8.0 mils diameter |
| Topside Metal: | Al (30,000Å) |
| Backside Metal: | Au (6,000Å) |
| Gross Die per 4” wafer: | 34,368 |

**Figure 2:CPD66X Chip Geometry**



| | |
|---|---|
| Die Size: | 17.5 x 17.5 mils |
| Die Thickness: | 5.9 mils |
| Bond Pad Area (Anode): | 8.0 mils diameter |
| Topside Metal: | Al (30,000Å) |
| Backside Metal: | Au-As (13,000Å) |
| Gross Die per 5” wafer: | 54,848 |

**Part Numbers Affected:**

CPD64-CLL459A-CT
CPD64-CMPD3003-CT
CPD64-CMPD3003-WN
CPD64-1N3595-CT
CPD64-1N3595-WN
CPD64-1N3595-WR
CPD64-1N457A-CT
CPD64-1N485B-CT

CMDD3003
CMLD3003DOG
CMOD3003
CMPD3003
CMPD3003A
CMPD3003C
CMPD3003S
CMHD457A
CMHD459A
CMHD3595